EAST Search History

S39	2	"5338959".pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 11:46
S40	5	"2004036118".pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 11:50
S41	2	"2004198003".pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 11:53
S42	2	"2004198003".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 12:00
S43	1703	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 12:15
S49	1487	438/197.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 12:02
S50	977	438/199.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 18:13
S51	319	438/157.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 13:30
S52	331	438/283.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 14:07
S53	1304	438/303.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 15:11

EAST Search History

S54	575	438/231.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 16:21
S55	1038	438/275.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 16:56
S56	12	("20030098488"|"20030201458"|"20040180491"|"20040262683"|"6635909"|"6858478").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 18:15
S57	44	("20020166838"|"20030122186"|"20030151077"|"20040036118"|"20040036127"|"20040092062"|"20040092067"|"20040094807"|"20040110097"|"20040191980"|"20040198003"|"20040238887"|"20040262699"|"20050127362"|"20050145941"|"5338959"|"5563077"|"6475890"|"6475890"|"6562665"|"6706571"|"6764884"|"6921982").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 18:17
S58	13	("20020081794" | "20020167007" | "5563077" | "5578513" | "5658806" | "5716879" | "6376317" | "6413802" | "6475869" | "6483156" | "6611029" | "6680240" | "6716684").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/19 12:36
S59	1646	work function same gate electrode	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/04/19 13:55
S60	119	work function same gate electrode and "3.9"	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/04/19 13:55

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	32	("6483156"|"20020167007"|"6716684"|"6475869"|"20020081794"|"6376317"|"5716879"|"5563077"|"6680240"|"5578513"|"5658806"|"6562665"|"6525403"|"5346839"|"6413802"|"6730964"|"6611029").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/16 10:12
S2	0	S1 and metal adj film and opposite adj sidewalls	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:14
S3	1	S1 and metal adj film	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:34
S4	83	opposite adj sidewall and gate adj electrode and gate adj dielectric	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:39
S5	23	opposite adj sidewall and gate adj electrode and gate adj dielectric and SOI	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:22
S6	92	("4589928" "5923066" "6090713" "4261761" "4863562" "5455547" "5537083" "5589082" "6218208" "6218208" "4249190" "6147381" "5952701" "4466175" "4899202" "4906587" "4946799" "4965213" "5293058" "5808346" "5930630" "6194289" "4270137" "4786609" "5397720" "5508555" "5541436" "5821575" "5877978" "5918114" "5930605" "6040212" "6060364" "6081443" "6124613" "6225662" "6225662" "6228698" "6238960" "4378628" "4460911" "4476545" "4599576" "4823180" "4929991" "4969022" "5442584" "5504027" "5663578" "5696396").pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:44
S7	1	opposite adj sidewall near5 semiconductor adj body and gate adj electrode and gate adj dielectric and SOI	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:23

EAST Search History

S8	13	("20020081794" | "20020167007" | "5563077" | "5578513" | "5658806" | "5716879" | "6376317" | "6413802" | "6475869" | "6483156" | "6611029" | "6680240" | "6716684").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/16 12:53
S9	6180	gate electrode and work function and metal film	US-PGPUB; USPAT; USOCR	AND	OFF	2005/03/16 12:53
S11	3561	gate electrode and work function same metal film	US-PGPUB; USPAT; USOCR	AND	ON	2005/03/16 12:55
S12	1901	gate electrode same work function same metal film	US-PGPUB; USPAT; USOCR	AND	ON	2005/03/16 12:56
S13	847	gate electrode same work function same metal film and p-type	US-PGPUB; USPAT; USOCR	AND	ON	2005/03/16 12:56
S14	49	gate electrode same work function same metal film	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/03/16 12:59
S15	350	work function same metal film	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/03/16 12:59
S16	149	work function same metal film and gate electrode	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/04/19 13:52
S17	4	"6858478".pn. "20040142567".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 11:01
S18	34	("20020081794"|"20020167007"|"5346839"|"5563077"|"5578513"|"5658806"|"5716879"|"6376317"|"6413802"|"6475869"|"6483156"|"6525403"|"6562665"|"6611029"|"6680240"|"6716684"|"6730964").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 12:58
S19	296	"18" and workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 12:58

S20	34	("20020081794"|"20020167007"|" 5346839"|"5563077"|"5578513"|" 5658806"|"5716879"|"6376317"|" 6413802"|"6475869"|"6483156"|" 6525403"|"6562665"|"6611029"|" 6680240"|"6716684"|"6730964"). PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 12:58
S21	1	S20 and workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 13:14
S22	99	gate adj electrode same workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:53
S23	260	gate same workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:58
S24	319	semiconductor and workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 16:20
S25	304	MOS$3 and workfunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:57
S26	348	S24 or S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:57
S27	275	S24 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 14:57
S28	11	gate same workfunction and "4.0"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 15:00

S29	11	gate and workfunction and "4.0"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 15:04
S30	279	gate and workfunction and "4"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 15:05
S31	38	gate and workfunction same "4"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 15:05
S32	1	semiconductor and workfunction same "4$3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 16:17
S33	9	finfet and metal adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 12:03
S34	403	finfet and metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 12:03
S35	253	finfet and metal near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 12:30
S36	190	finfet and metal near5 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 17:23
S37	35	finfet and metal near5 gate adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/08 17:23
S38	2	"6562665".pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/18 11:42